



CMLT3410 CMLT3410G* NPN
 CMLT7410 CMLT7410G* PNP
 CMLT3474 CMLT3474G* NPN/PNP

**SURFACE MOUNT PICOmini™
 DUAL LOW $V_{CE(SAT)}$
 SILICON TRANSISTORS**

PICOmini™



SOT-563 CASE

Central™ Semiconductor Corp.

DESCRIPTION:

These dual devices are low $V_{CE(SAT)}$ silicon transistors in a PICOmini™ surface mount package designed for small signal general purpose amplifier and switching applications requiring low collector emitter saturation voltage.

MARKING CODES:

CMLT3410: C34 CMLT3410G: 34G
CMLT7410: C74 CMLT7410G: 74G
CMLT3474: C37 CMLT3474G: 37G

* Device is **Halogen Free** by design

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	1.0	A
Collector Current (Peak)	I_{CM}	1.5	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

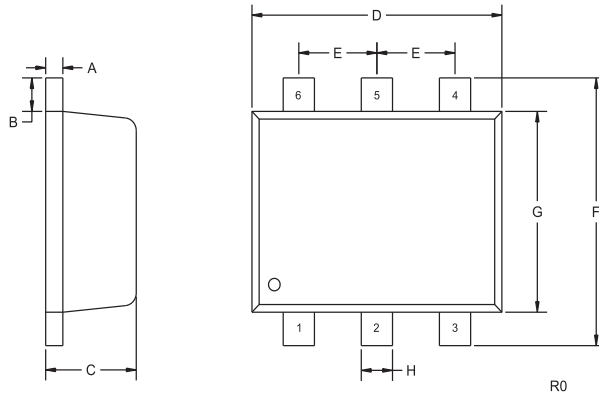
ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP			MAX	UNITS
		MIN	NPN	PNP		
I_{CBO}	$V_{CB}=40\text{V}$				100	nA
I_{EBO}	$V_{EB}=6.0\text{V}$				100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	40				V
BV_{CEO}	$I_C=10\text{mA}$	25				V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0				V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		20	25	50	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		35	40	75	mV
$V_{CE(SAT)}$	$I_C=200\text{mA}, I_B=20\text{mA}$		75	80	150	mV
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		130	150	250	mV
$V_{CE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$		200	220	400	mV
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		250	275	450	mV
$V_{BE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$				1.1	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$				0.9	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100				
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	100			300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	100				
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$	50				
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	100				MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$ (CMLT3410)				10	pF
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$ (CMLT7410)				15	pF

R1 (7-April 2009)

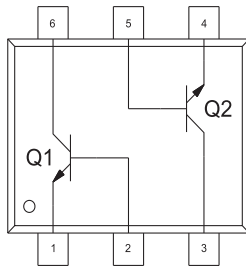
**SURFACE MOUNT PICOMini[™]
DUAL LOW $V_{CE(SAT)}$
SILICON TRANSISTORS**

SOT-563 CASE - MECHANICAL OUTLINE

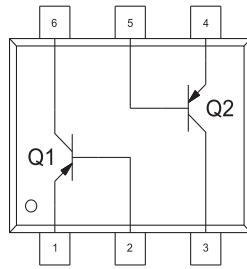


SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

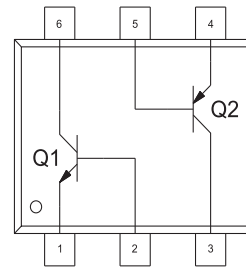
SOT-563 (REV: R0)



MARKING CODE
CMLT3410: C34
CMLT3410G: 34G



MARKING CODE
CMLT7410: C74
CMLT7410G: 74G



MARKING CODE
CMLT3474: C37
CMLT3474G: 37G

LEAD CODE:

- 1) EMITTER Q1
- 2) BASE Q1
- 3) COLLECTOR Q2
- 4) EMITTER Q2
- 5) BASE Q2
- 6) COLLECTOR Q1